

# MSKSEMI 美森科

SEMICONDUCTOR



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## AONS32304

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Product specification

## Description

The AONS32304 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## Features

$V_{DS} = 30V$   $I_D = 150A$

$R_{DS(ON)} < 2.4m\Omega$   $V_{GS} = 10V$

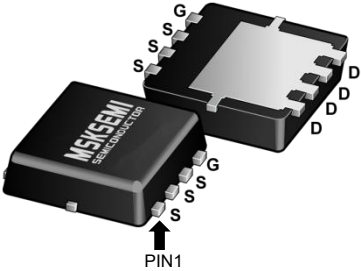
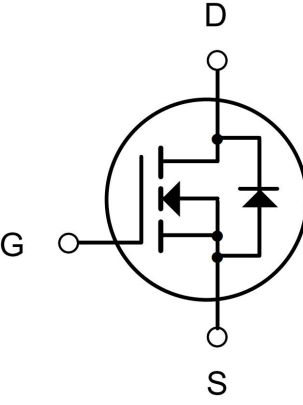

## Application

Battery protection

Load switch

Uninterruptible power supply

## Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 <p>DFN5X6-8L</p>		

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain- Source Voltage	30	V
$V_{GS}$	Gate- Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>1</sup>	150	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ <sup>1</sup>	80	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	160	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	180	mJ
$I_{AS}$	Avalanche Current	60	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>4</sup>	187	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction- Ambient <sup>1</sup>	62	°C/ W
$R_{\theta JC}$	Thermal Resistance Junction- Case <sup>1</sup>	1.1	°C/ W

**Electrical Characteristics (TA=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to 25°C, $I_D=1mA$	---	0.014	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	2	2.4	mΩ
		$V_{GS}=4.5V, I_D=15A$	---	2.5	3.2	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	MV/°C
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	±100	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	50	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.7	---	Ω
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=10V, I_D=15A$	---	56.9	---	nC
$Q_{gs}$	Gate-Source Charge		---	13.8	---	
$Q_{gd}$	Gate-Drain Charge		---	23.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=1A$	---	20.1	---	ns
$T_r$	Rise Time		---	6.3	---	
$T_{d(off)}$	Turn-Off Delay Time		---	124.6	---	
$T_f$	Fall Time		---	15.8	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	4345	---	pF
$C_{oss}$	Output Capacitance		---	340	---	
$C_{riss}$	Reverse Transfer Capacitance		---	225	---	

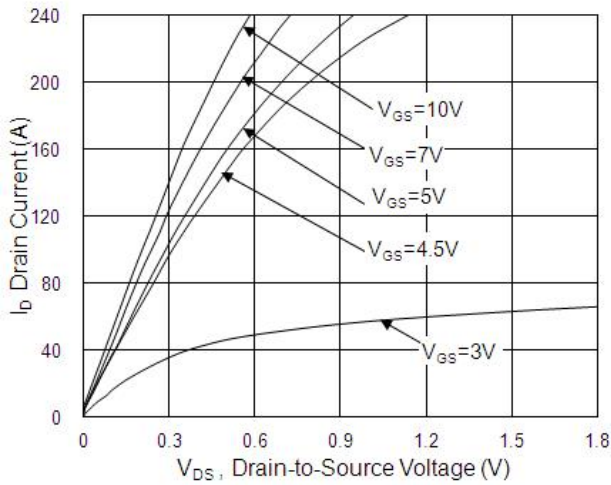
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	150	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V

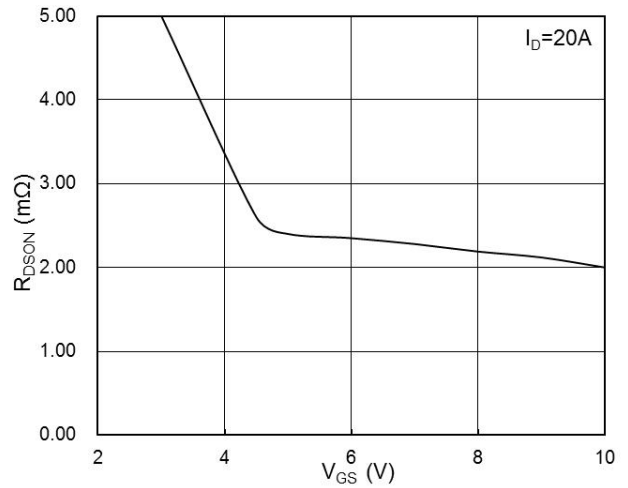
**Note :**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup>FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=60A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.

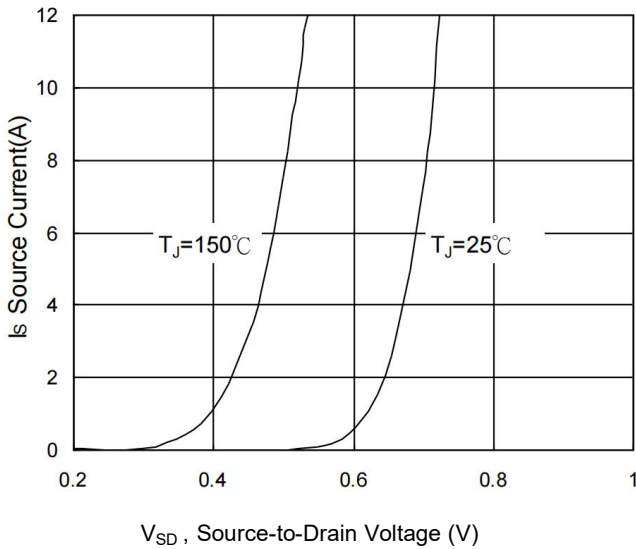
**Typical Characteristics**



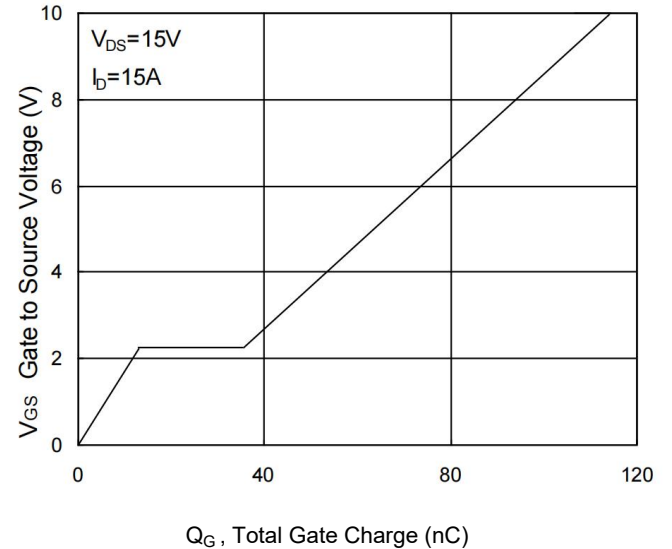
**Fig.1 Typical Output Characteristics**



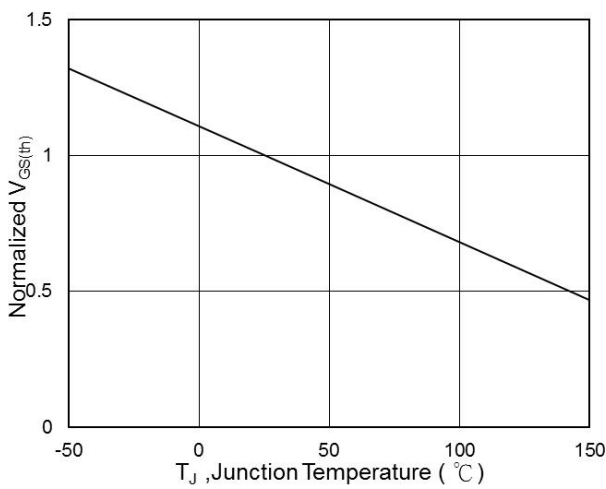
**Fig.2 On-Resistance v.s Gate-Source**



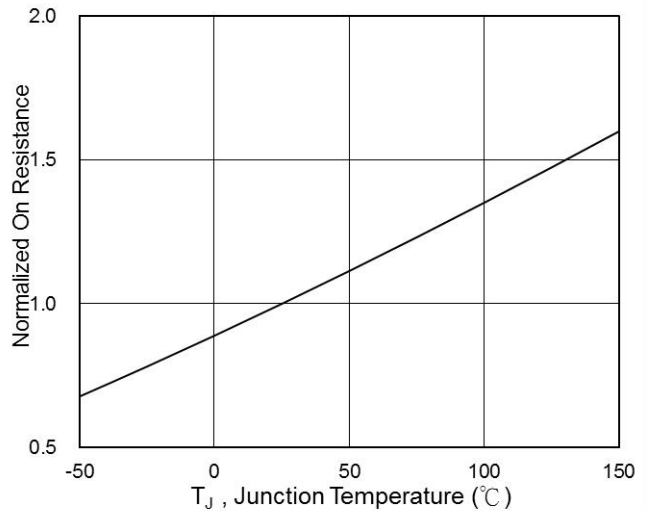
**Fig.3 Forward Characteristics of Reverse**



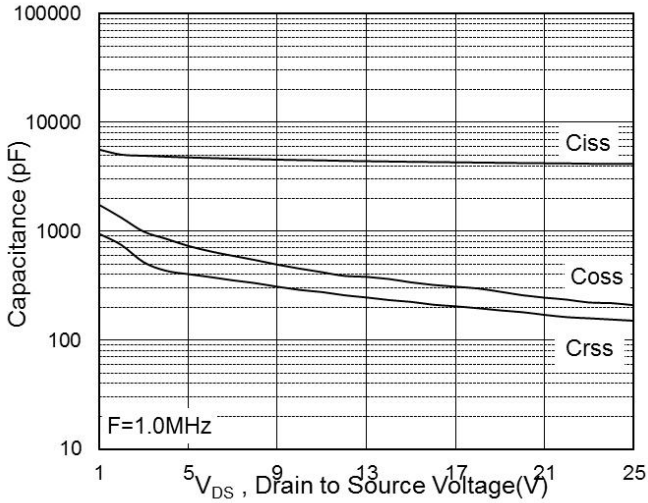
**Fig.4 Gate-Charge Characteristics**



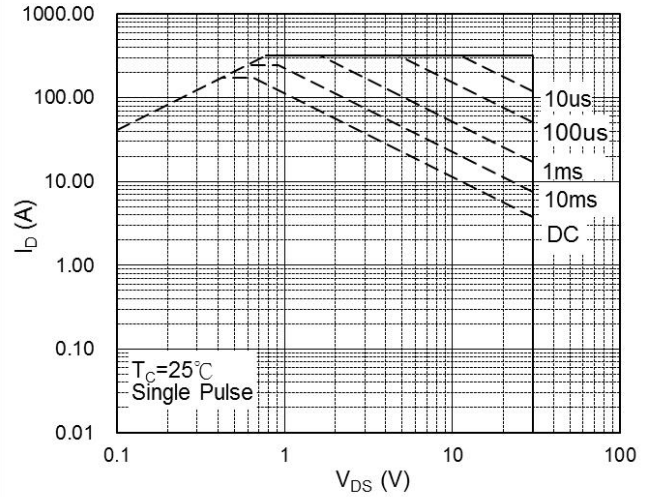
**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



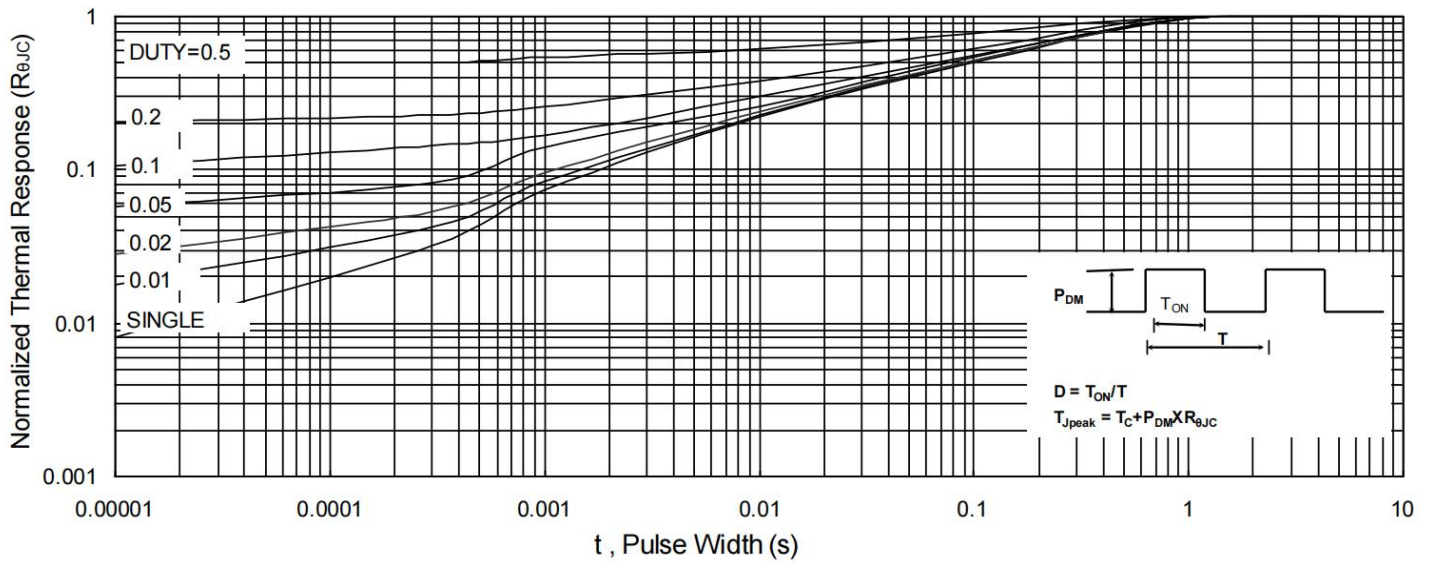
**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**



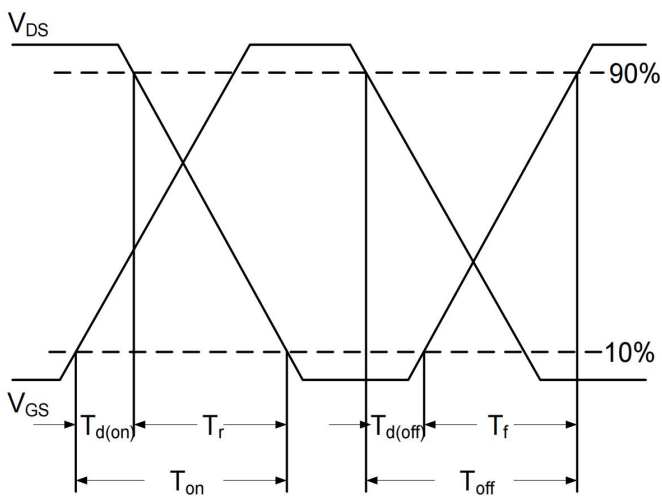
**Fig.7 Capacitance**



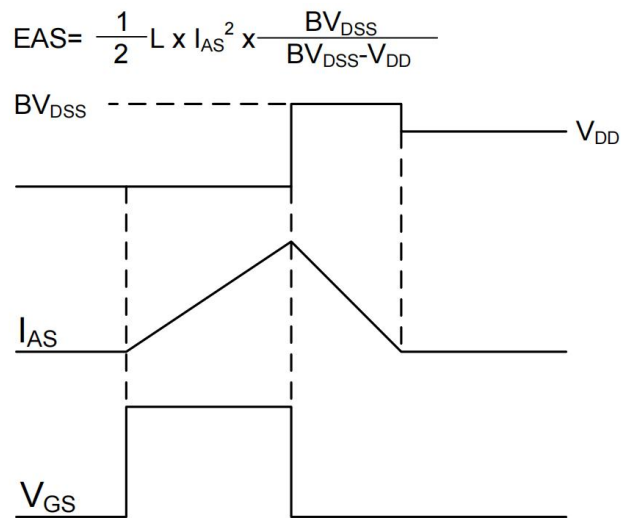
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



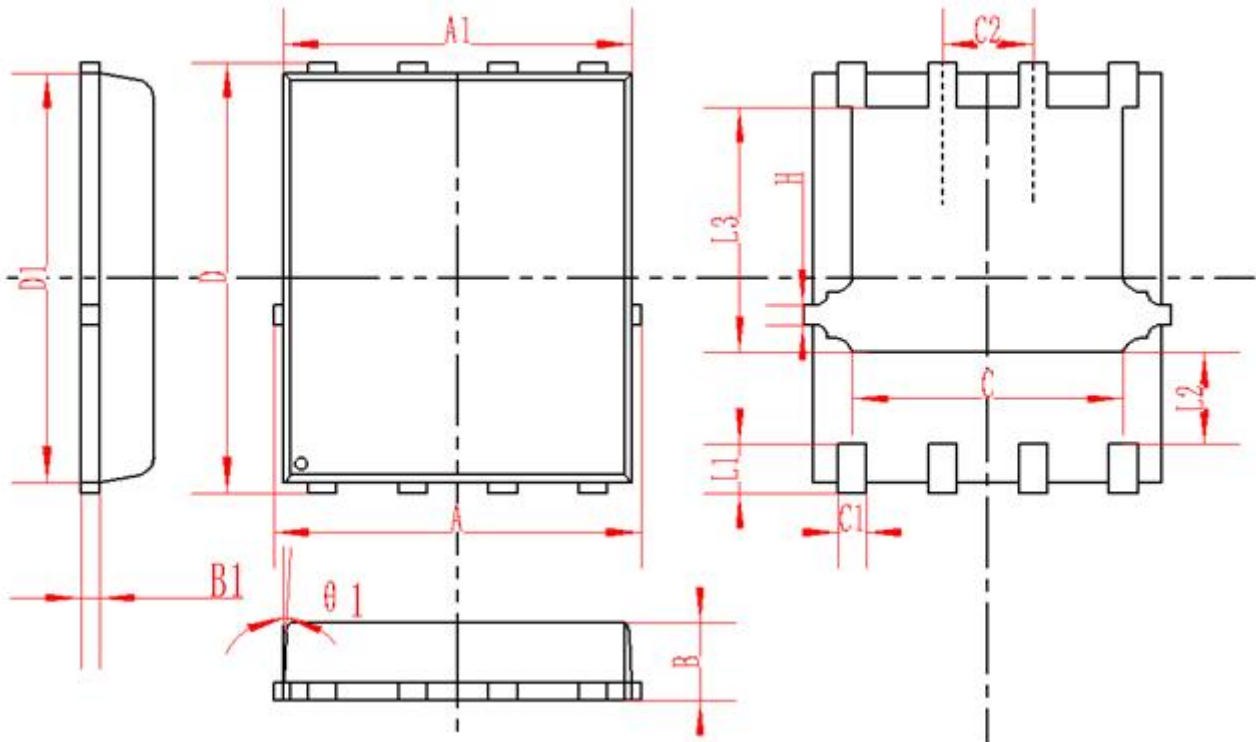
**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

**DFN5X6-8L Package Information**



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

**REEL SPECIFICATION**

P/N	PKG	QTY
AONS32304	DFN5X6-8L	5000



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